

## General Description

The WSF18N15 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSF18N15 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

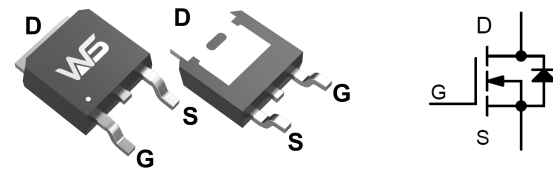
## Product Summary

$BV_{DSS}$	$R_{DSON}$	$I_D$
150V	95mΩ	17A

## Applications

- High-Frequency Switch
- Load Switch
- Motion Switch

## TO-252 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	150	V
$V_{GS}$	Gate-Source Voltage	±20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	17	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	12	A
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	3.0	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	2.5	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	40	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	53	mJ
$I_{AS}$	Avalanche Current	18	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation <sup>3</sup>	72.6	W
$P_D@T_A=25^{\circ}C$	Total Power Dissipation <sup>3</sup>	2.1	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	60	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	1.72	°C/W

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	150	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.098	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	---	95	105	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	105	115	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	---	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.57	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =120V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =120V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =10A	---	33	---	S
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =75V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	25.1	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	6.8	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	12.6	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =25V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =10A.	---	13	---	ns
T <sub>r</sub>	Rise Time		---	8.2	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	25	---	
T <sub>f</sub>	Fall Time		---	11	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz	---	2285	---	pF
C <sub>oss</sub>	Output Capacitance		---	110	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	83	---	

**Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	V <sub>DD</sub> =25V, L=0.5mH, I <sub>AS</sub> =6A	15	---	---	mJ

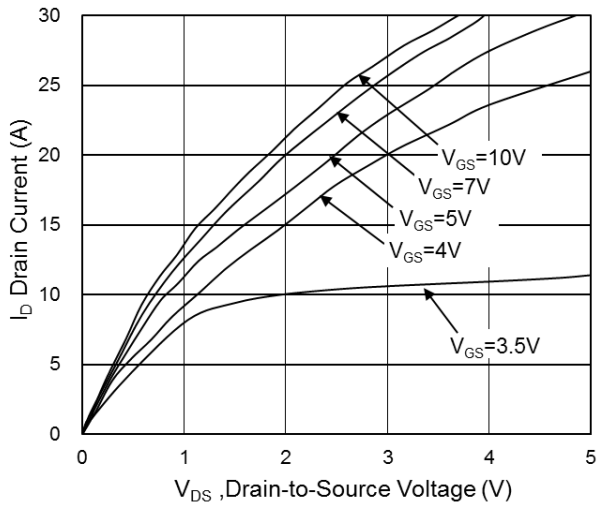
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	17	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>		---	---	40	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =10A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	37	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	263	---	nC

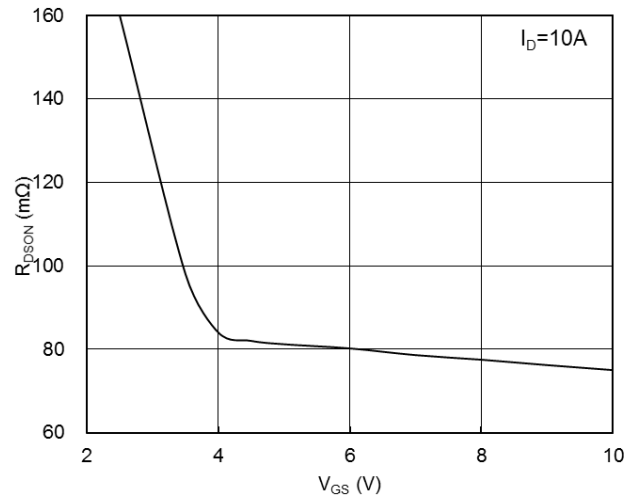
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3 .The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V,V<sub>GS</sub>=10V,L=0.3mH,I<sub>AS</sub>=18A
- 4.The power dissipation is limited by 150°C junction temperature
- 5 .The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

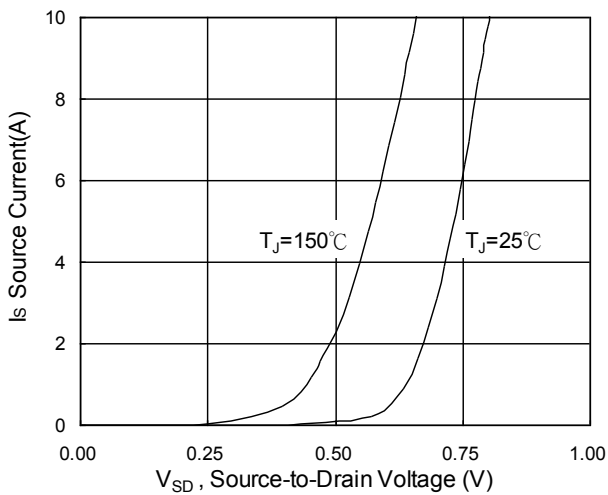
**Typical Characteristics**



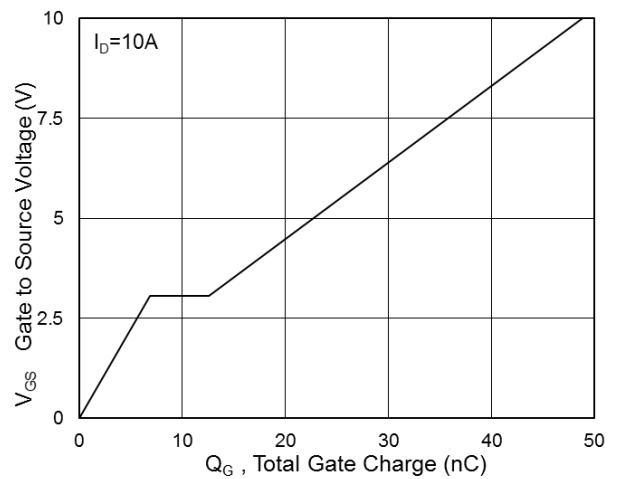
**Fig.1 Typical Output Characteristics**



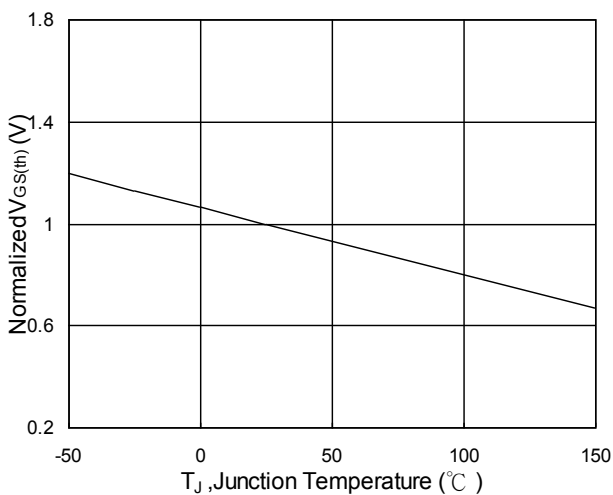
**Fig.2 On-Resistance vs. Gate-Source Voltage**



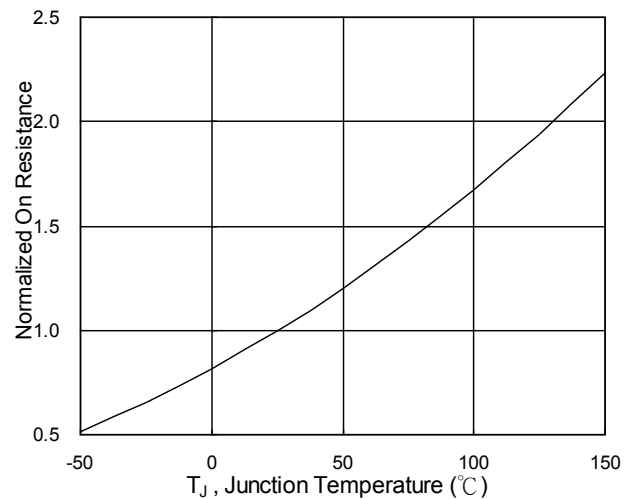
**Fig.3 Forward Characteristics of Reverse**



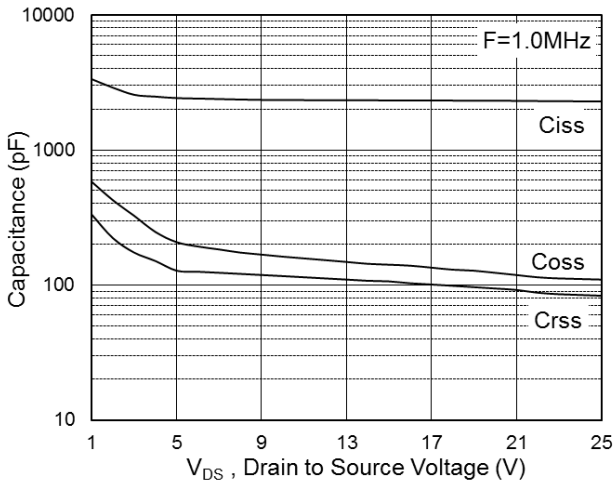
**Fig.4 Gate-Charge Characteristics**



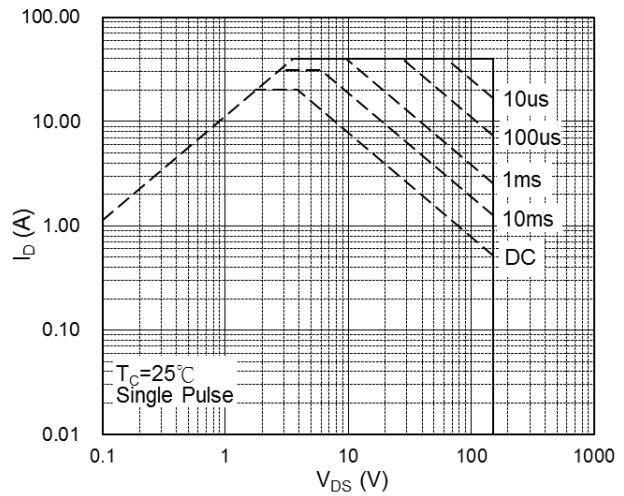
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



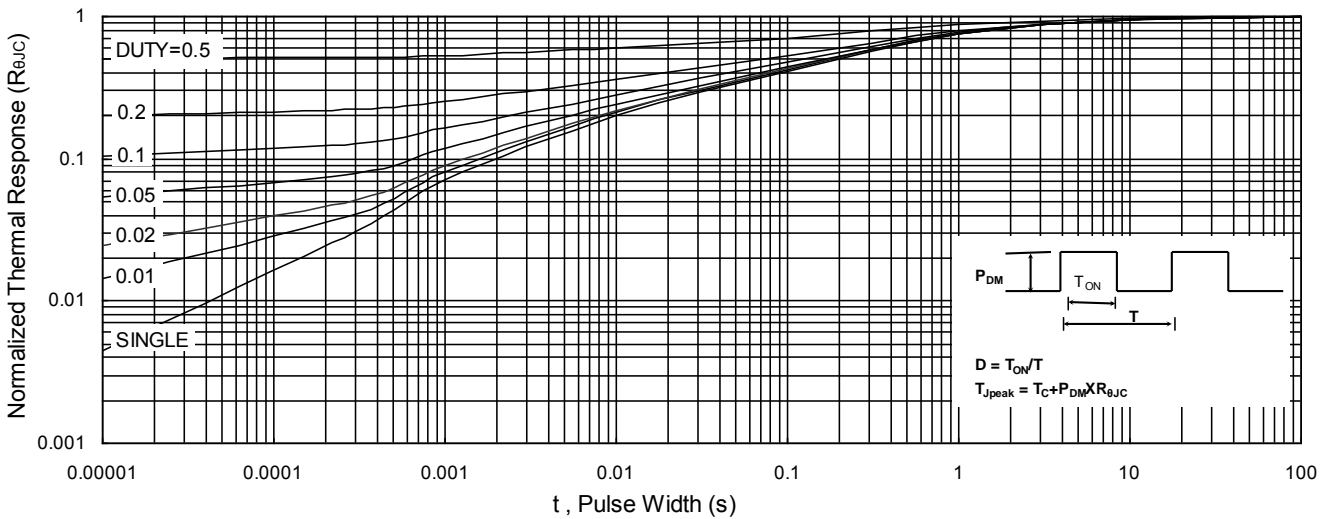
**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



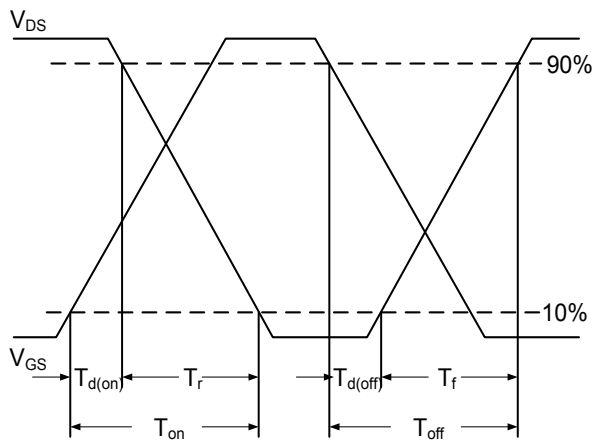
**Fig.7 Capacitance**



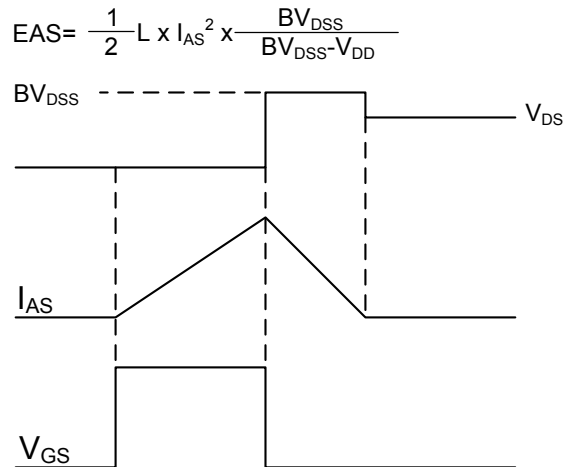
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching Waveform**



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